

Replacement Claims

1. (amended) A method of fabricating a semiconductor device, the method comprising:

depositing an oxygen-deficient dielectric film; and

A1            subjecting the dielectric film to a wet oxidation in a rapid thermal process chamber at a temperature of at least about 450 °C and for a duration which increases the oxygen content of the dielectric film but does not allow an oxidizing species to diffuse through the dielectric film into a layer underlying the dielectric film.